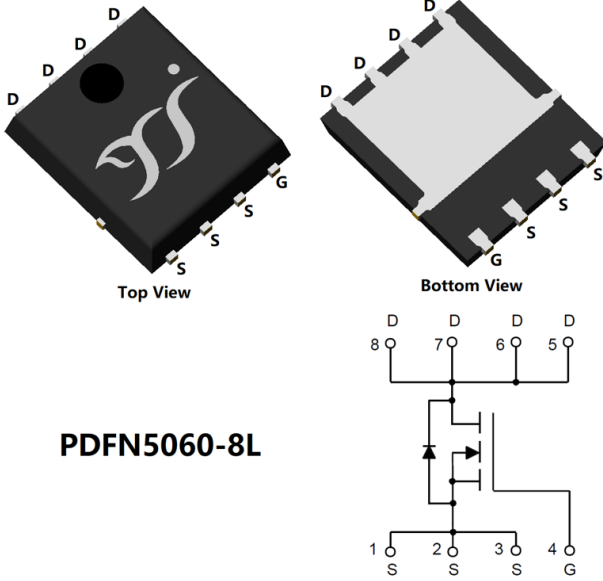


## N-Channel Enhancement Mode Field Effect Transistor



PDFN5060-8L

### Product Summary

- $V_{DS}$  60V
- $I_D$  30A
- $R_{DS(ON)}$  ( at  $V_{GS}=10V$ )  $<21m\Omega$
- $R_{DS(ON)}$  ( at  $V_{GS}=4.5V$ )  $<26m\Omega$
- 100% EAS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Part no. with suffix "Q" means AEC-Q101 qualified

### Applications

- Power switching application
- Uninterruptible power supply
- DC-DC convertor
- 12V and 24V Automotive systems

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	60	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25^\circ C$	$I_D$	7.3	A
	$T_A=100^\circ C$		4.7	
	$T_C=25^\circ C$		30	
	$T_C=100^\circ C$		19	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	120	A
Avalanche energy <sup>B</sup>		EAS	90	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25^\circ C$	$P_D$	2.5	W
	$T_A=100^\circ C$		1	
	$T_C=25^\circ C$		44.5	
	$T_C=100^\circ C$		17.8	
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	2.8	$^\circ C/W$
Thermal Resistance Junction-to-Ambient <sup>D</sup>		$R_{\theta JA}$	50	$^\circ C/W$
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG30N06AQ	F1	YJG30N06A	5000	10000	100000	13" reel



# YJG30N06AQ

## ■ Electrical Characteristics ( $T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V, V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=15A$		16	21	m $\Omega$
		$V_{GS}=4.5V, I_D=10A$		17	26	m $\Omega$
Diode Forward Voltage	$V_{SD}$	$I_S=15A, V_{GS}=0V$		0.85	1.2	V
Gate resistance	$R_G$	$f=1\text{MHz}$		1		$\Omega$
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$		2450		pF
Output Capacitance	$C_{oss}$			165		
Reverse Transfer Capacitance	$C_{rss}$			125		
<b>Switching Parameters</b>						
Total Gate Charge	$Q_g$	$V_{GS}=10V, V_{DS}=30V, I_D=20A$	-	46	-	nC
Gate-Source Charge	$Q_{gs}$		-	6	-	
Gate-Drain Charge	$Q_{gd}$		-	11	-	
Reverse Recovery Charge	$Q_{rr}$	$I_F=20A, di/dt=100A/\mu s$	-	28.2	-	nC
Reverse Recovery Time	$t_{rr}$		-	32	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=30V, I_D=20A$	-	9	-	ns
Turn-on Rise Time	$t_r$		-	41	-	
Turn-off Delay Time	$t_{D(off)}$		-	28	-	
Turn-off fall Time	$t_f$		-	2.8	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B.  $T_J=25^\circ\text{C}$ ,  $V_{DD}=40V$ ,  $V_G=10V$ ,  $L=0.5\text{mH}$ ,  $I_{AS}=19A$ .

C.  $P_g$  is based on max. junction temperature, using junction-case thermal resistance.

D. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with  $T_A=25^\circ\text{C}$ . The maximum allowed junction temperature of  $150^\circ\text{C}$ . The value in any given application depends on the user's specific board design.



# YJG30N06AQ

## Typical Electrical and Thermal Characteristics Diagrams

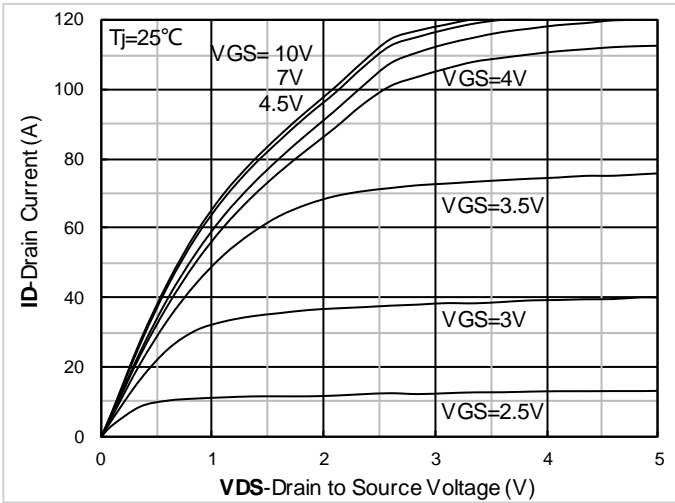


Figure 1. Output Characteristics

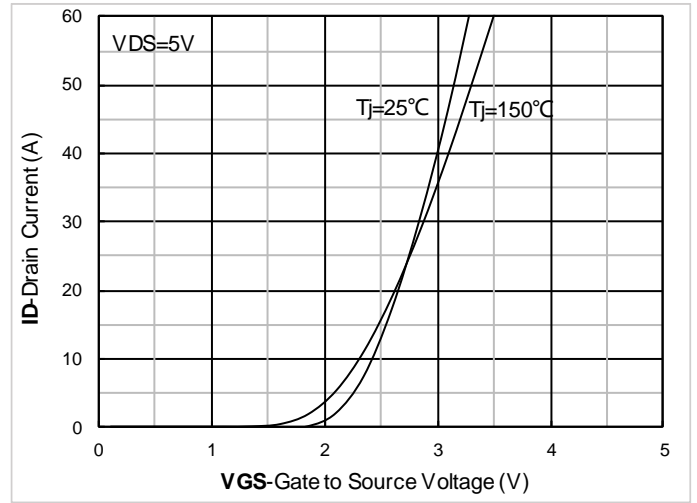


Figure 2. Transfer Characteristics

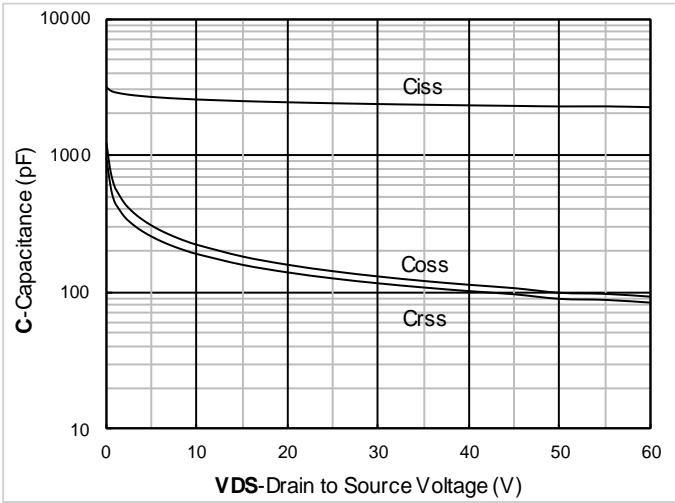


Figure 3. Capacitance Characteristics

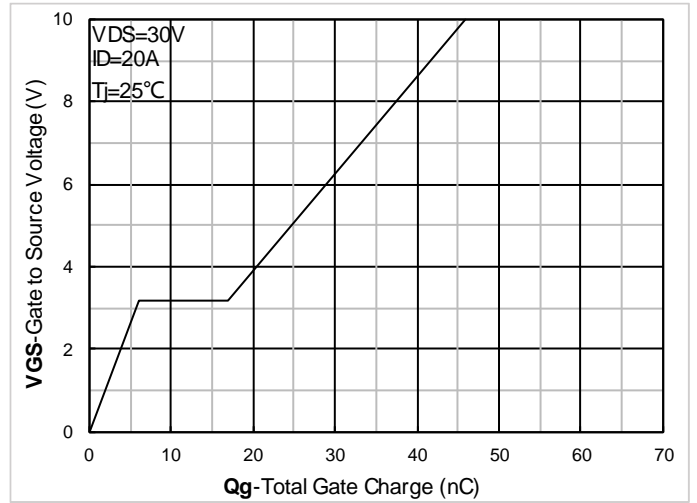


Figure 4. Gate Charge

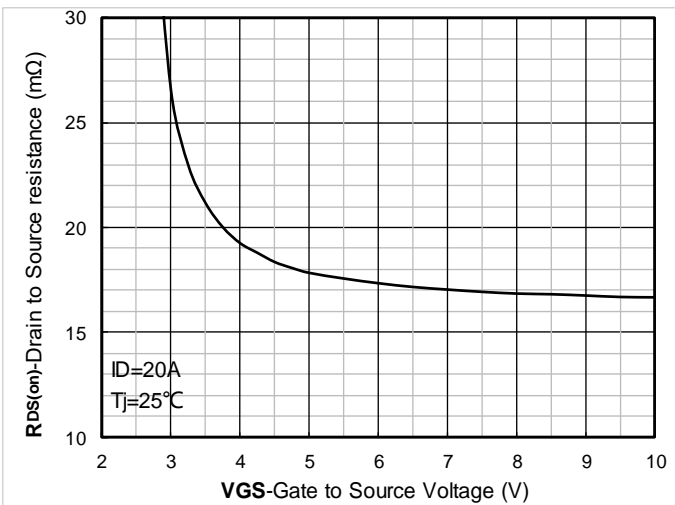


Figure 5. On-Resistance vs Gate to Source Voltage

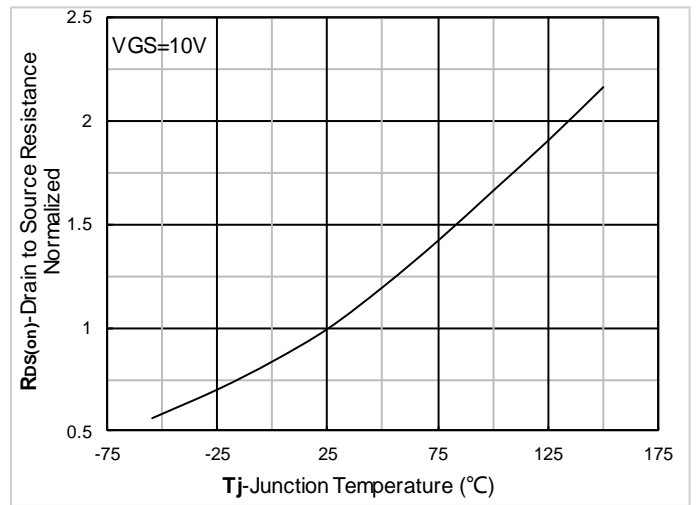


Figure 6. Normalized On-Resistance

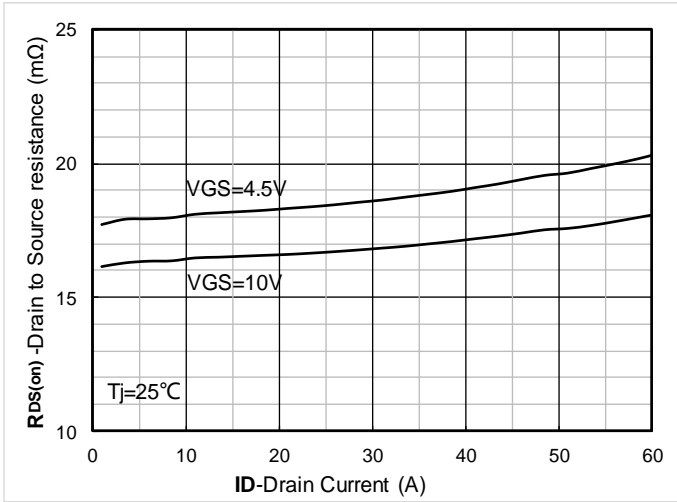


Figure 7. RDS(on) VS Drain Current

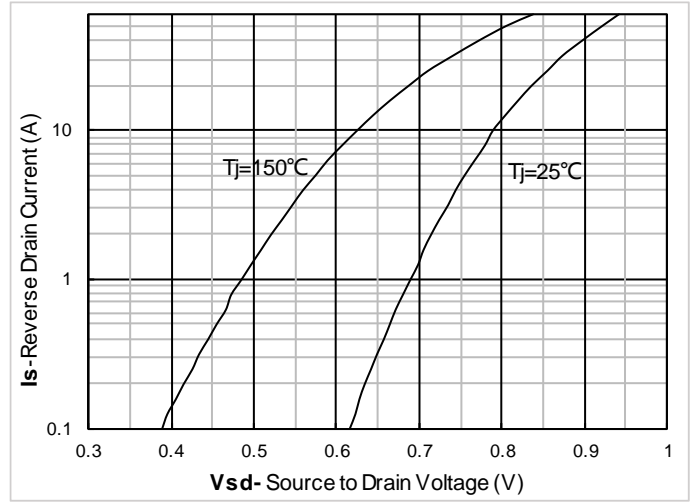


Figure 8. Forward characteristics of reverse diode

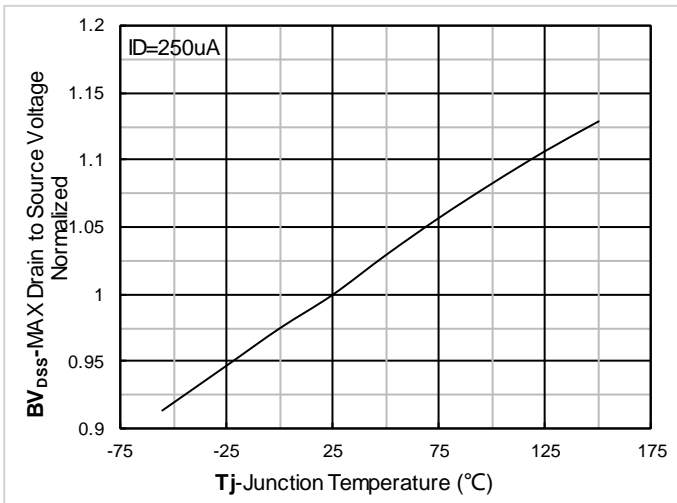


Figure 9. Normalized breakdown voltage

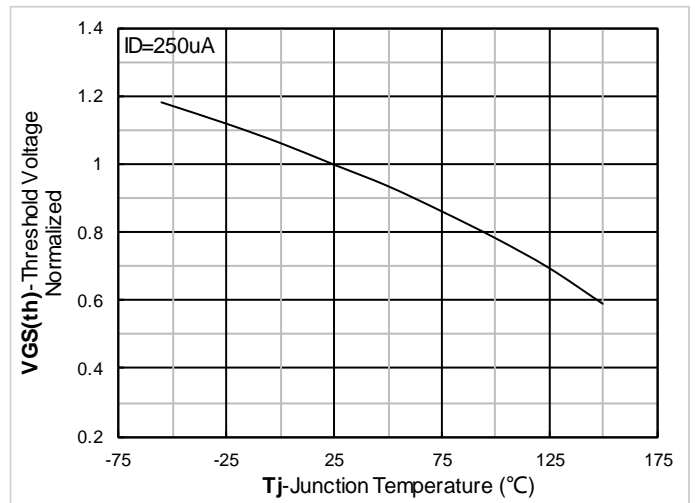


Figure 10. Normalized Threshold voltage

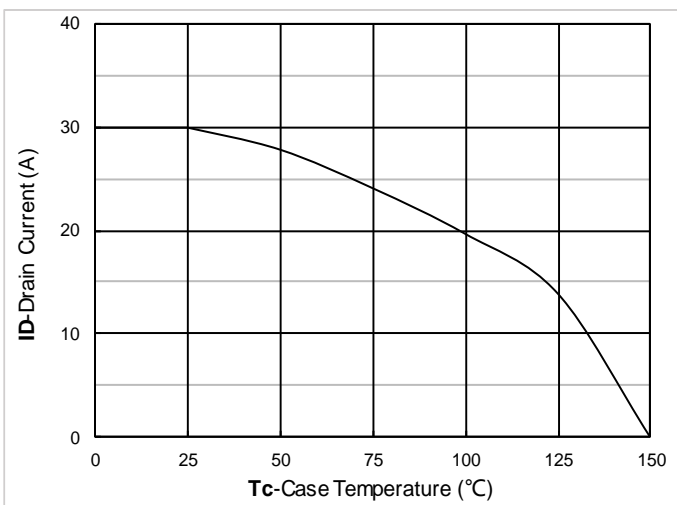


Figure 11. Current dissipation

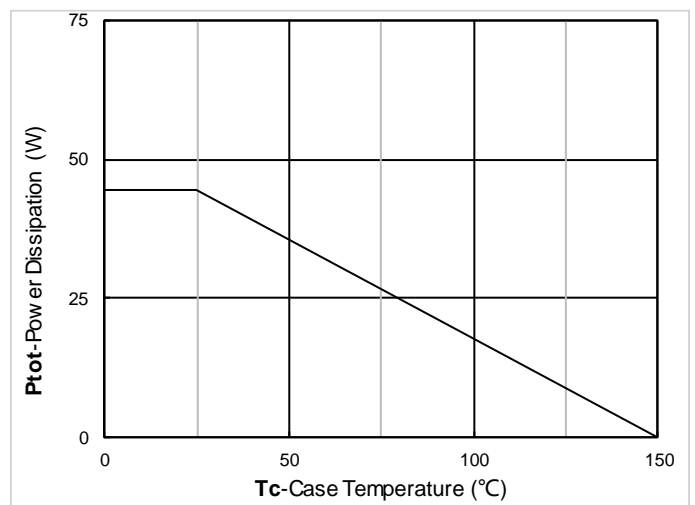


Figure 12. Power dissipation



# YJG30N06AQ

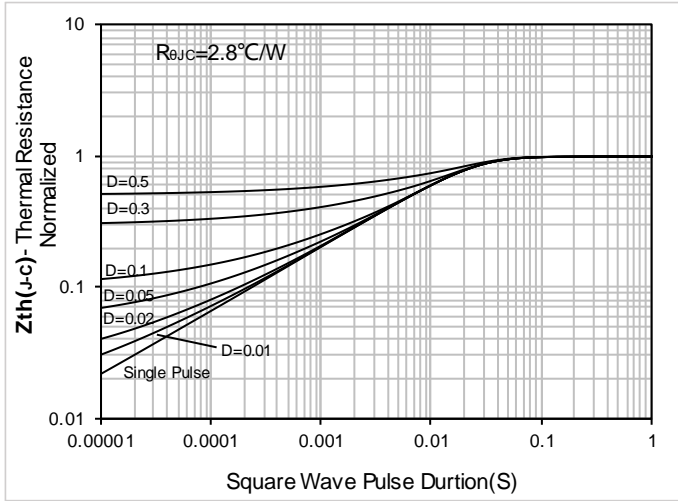


Figure 13. Maximum Transient Thermal Impedance

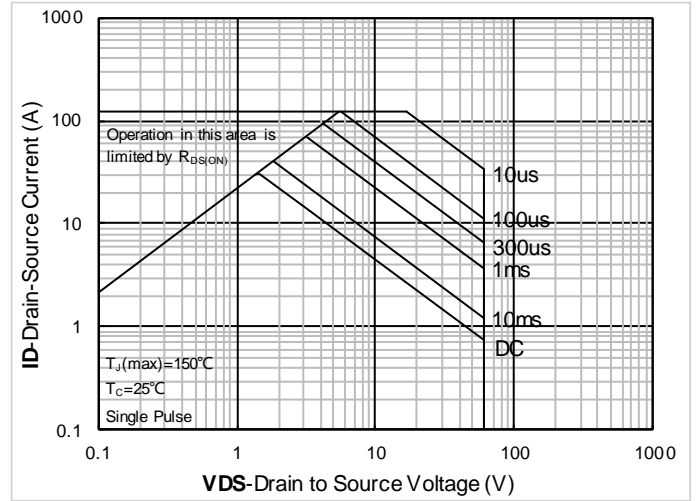
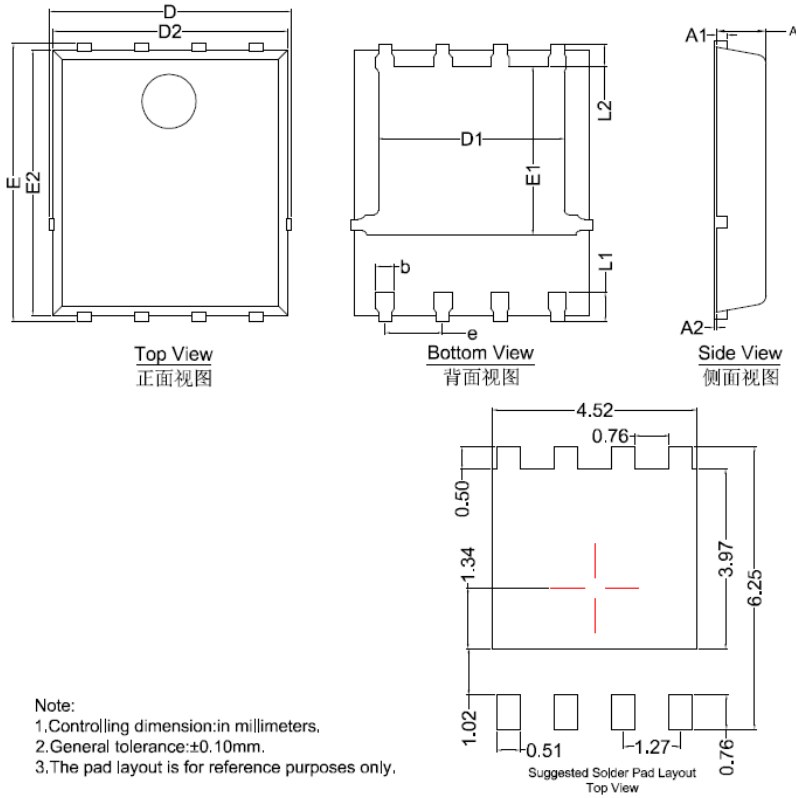


Figure 14. Safe Operation Area



# YJG30N06AQ

## ■ PDFN5060-8L-1.1MM Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance:  $\pm 0.10$ mm.  
 3. The pad layout is for reference purposes only.



## YJG30N06AQ

---

### Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with automotive electronics, are not designed for use in medical, life-saving, lifesustaining, or military, Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com> , or consult your nearest Yangjie's sales office for further assistance.